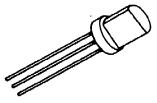
20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

Voltages



Silicon Transistor

2N3721 is a NPN silicon transistor intended for general purpose applications. The planar passivated construction assures excellent device stability and life. This high performance, high value device is made possible by utilizing advanced manufacturing techniques and epoxy encapsulation.



TELEPHONE: (973) 376-2922

(212) 227-6005

FAX: (973) 376-8960

absolute maximum ratings: (25°C) (unless otherwise specified)

| t on ages | | | | | |
|-------------------------------------|------------------|-------------------|------------------------|-------------------------------|--|
| Collector to emitter | V _{CEO} | 18 | V | | <u>05</u> 95 - |
| Emitter to base | V _{EBO} | 5 | V | 뿌~뿌 | 83 - |
| Collector to base | V _{CBO} | 18 | V NOTE 1: Lead | diameter is controlled in the | |
| Current | | | ing plane. Betv | ween .250 and end of lead a | .075 .055 .265 .225 |
| Collector (steady state) | I _C . | 100 | maix: of .021 i mA. | | .225 |
| Dissipation | | | | ודק | .500 SEATING |
| Total Power (Free air @ 25°C) | P _T | 360 | mW ALL DIMEN. | IN INCHES AND ARE | MIN PLANE |
| Total Power (Free air @ 55°C) | P _T | 260 | mW | !- | 050±.005 |
| Temperature | | | | 3 LEADS | |
| Storage | T _{STG} | -55 to | +125°C | .017 +.002 | .090 |
| Operating | T, | | +125° C | (NOTE I) | $(\frac{1}{2}, \frac{1}{2}, $ |
| * Determined from nower limitations | due to seturet | ion voltage at th | c overant | E. | |

Determined from power limitations due to saturation voltage at this current.

** Derate 2.67 mW/°C increase in ambient temperature above 25°C.

electrical characteristics: (25°C) (unless otherwise specified)

| DC Characteristics Collector cutoff current: (VCB = 18V) (VCB = 18V, TA=100°C) Emitter cutoff current: (VEB=5V) Small Signal Characteristics | I _{cbo} I _{cbo} I _{ebo} | Min. | Тур. | Max. 0.5 15 0.5 | Units μΑ μΑ μΑ |
|--|--|------|------|--------------------------|-------------------------|
| Forward current transfer ratio: (VCE=) | 10V, | | | | |
| $IC = 2 ma, f = lk Hz^{\dagger}$ | h _{FE} | 60 | | 660 | |
| Input impedance: | | | | | |
| (VCE=10V, IC=2mA, f=lk Hz) | h _{IB} | | 15 | | ohms |
| High Frequency Characteristics | | | | | |
| Collector capacitance: (VCB=10V, IE= | О, | | | | |
| f=l MHz) | C _{cb} | 4.5 | 7 | 10 | pF |
| Gain bandwidth product: | | | | | • |
| (IC=4mA, VCB=5V) | f _i | | 120 | | MHz |

† Hz=Hertz, equivalent to cycles per second.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information turnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datachaste are corrent before obeing orders.